N-Channel MOS Silicon FET



## **CPH6402**

# **Ultrahigh-Speed Switching Applications**

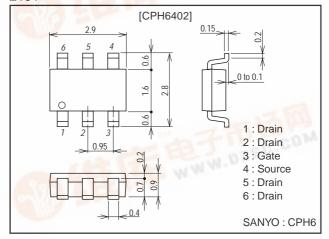
#### **Features**

- · Low ON resistance.
- · Ultrahigh-speed switching.
- · 4V drive.

#### **Package Dimensions**

unit:mm

2151



## **Specifications**

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit	
Drain-to-Source Voltage	V <sub>DSS</sub>		30	V	
Gate-to-Source Voltage	V <sub>GSS</sub>		±24	V	
Drain Current (DC)	ID		4	Α	
Drain Current (pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	16	Α	
Allowable Power Dissipation	PD	Mounted on a ceramic board (900mm <sup>2</sup> ×0.8mm)	1.6	W	
Channel Temperature	Tch	AND ASSESSMENT OF THE PARTY OF	150	°C	
Storage Temperature	Tstg	130 14	-55 to +150	°C	

#### **Electrical Characteristics** at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	I <sub>D</sub> =1mA, V <sub>GS</sub> =0	30			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =30V, V <sub>GS</sub> =0			10	μΑ
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0			±10	μΑ
Cutoff Voltage	VGS(off)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	1.0		2.4	V
Forward Transfer Admittance	yfs	V <sub>DS</sub> =10V, I <sub>D</sub> =2A	3.0	4.3	7 7 7	S
Static Drain-to-Source On-State Resistance	R <sub>DS(on)</sub> 1	I <sub>D</sub> =2A, V <sub>GS</sub> =10V		55	75	mΩ
	R <sub>DS(on)</sub> 2	I <sub>D</sub> =1A, V <sub>GS</sub> =4V	and All	110	155	mΩ
Input Capacitance	Ciss	V <sub>DS</sub> =10V, f=1MHz		240		pF
Output Capacitance	Coss	V <sub>DS</sub> =10V, f=1MHz		160		pF
Reverse Transfer Capacitance	Crss	V <sub>DS</sub> =10V, f=1MHz		70		pF

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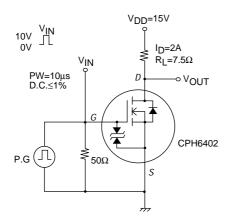


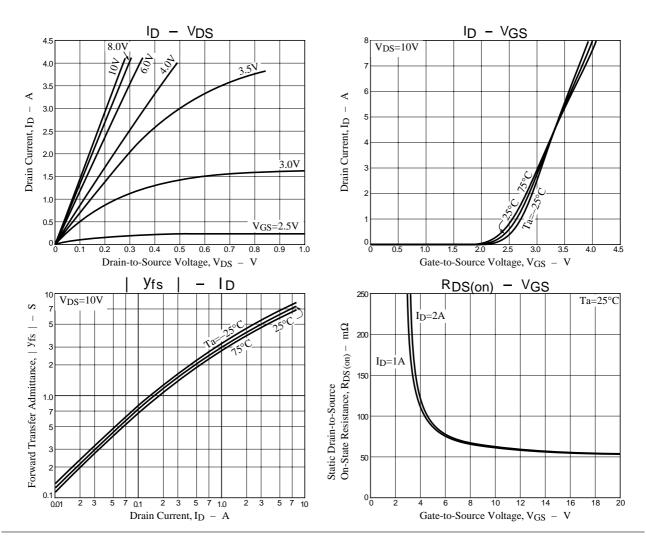
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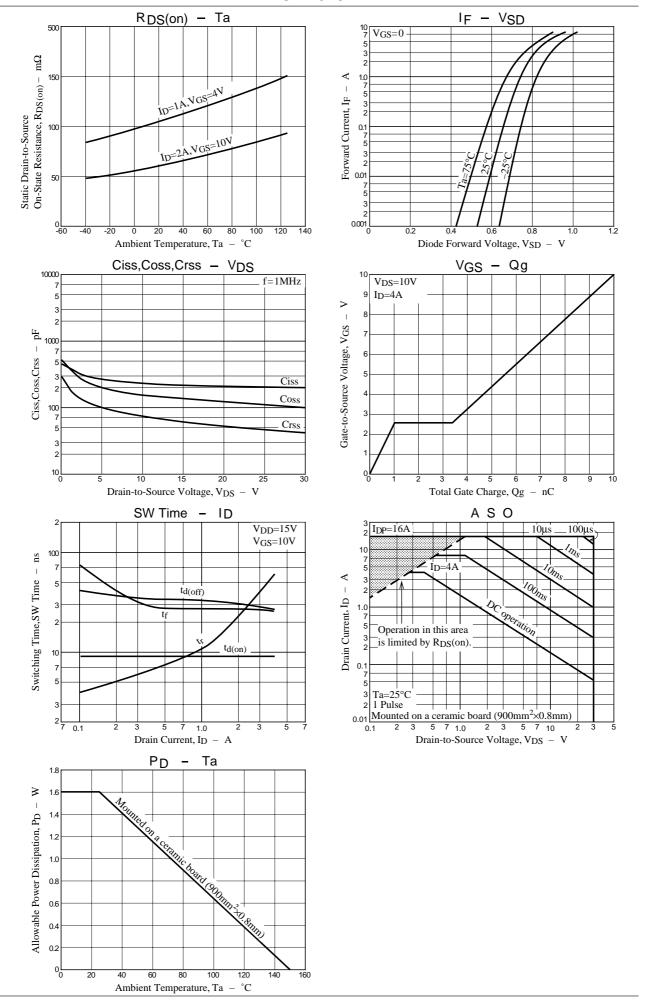
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	O'III
Turn-ON Delay Time	<sup>t</sup> d(on)	See specified Test Circuit		9		ns
Rise Time	t <sub>r</sub>	See specified Test Circuit		25		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit		30		ns
Fall Time	t <sub>f</sub>	See specified Test Circuit		28		ns
Total Gate Charge	Qg	V <sub>DS</sub> =10V, V <sub>GS</sub> =10V, I <sub>D</sub> =4A		10		nC
Gate-to-Source Charge	Qgs	V <sub>DS</sub> =10V, V <sub>GS</sub> =10V, I <sub>D</sub> =4A		1		nC
Gate-to-Drain "Miller" Charge	Qgd	V <sub>DS</sub> =10V, V <sub>GS</sub> =10V, I <sub>D</sub> =4A		2.4		nC
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =4A, V <sub>GS</sub> =0		0.85	1.2	V

## **Switching Time Test Circuit**





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